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				Application Number	10/606,176
				Filing Date	June 25, 2003
				First Named Inventor	Yoshihide Nakamura
				Art Unit	2811
				Examiner Name	Ori Nadav
Sheet		of		Attorney Docket Number	09792909-5625

[illegible][illegible]

Examiner Signature	<i>ON</i>	Date Considered	<i>2/20/07</i>
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Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete if Known</b>			
		Application Number	10/606,176		
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		Art Unit	2811		
Sheet		of		Examiner Name	Ori Nadav
				Attorney Docket Number	09792909-5625

OTHER ITEMS – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
ON		"InGaN Multi-Quantum-Well-Structure Laser Diodes with Cleaved Mirror Cavity Facets," Jpn. J. Appl. Phys., Vol. 35, 1996, pp. L217-L220	
		"Blue InGaN-Based Laser Diodes with an Emission Wavelength of 450nm" Appl. Phys. Lett., Vol. 76, 2000, pp. 22-24	
		"Fist III-V-Nitride-Based Violet Laser Diodes" J. Crystal Growth, Vol. 170, 1997, pp. 11-15	
		"High-Power, Long-Lifetime InGaN/GaN/AlGaIn-Based Laser Diodes Grown on Pure GaN Substrates." Jpn. J. Appl. Phys., Vol. 35, 1998, pp. L309-L312	
		"InGaN/GaN/AlGaIn-Based Laser Diodes Grown on Epitaxially Laterally Overgrown GaN," J. Mater. Res., Vol. 14, No. 7, 1999, pp. 2716-2731	
ON		"InGaN/GaN/AlGaIn-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices," Jpn. J. Appl. Phys., Vol. 36, 1997, pp. 1568-1571	

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